IN THE SPECIFICATION

Please amend the Title on page 1 as follows:

SEMICONDUCTOR DEVICE AND SEMICONDUCTOR ASSEMBLY MODULE WITH A GAP-CONTROLLING LEAD STRUCTURE

Please replace the paragraph at page 13, lines 8-22, with the following rewritten paragraph:

As shown in FIGs. 1A-1D to FIG. 3, in the semiconductor device of the embodiment 1, a power semiconductor element 2 and a control semiconductor element 3 are mounted on a copper lead frame 5 provided with a plurality of leads 4. Both of the semiconductor elements 2 and 3 are electrically connected to each other by their respectively corresponding leads 4 and metallic thin wires 6 and 7. Moreover, the semiconductor device 1 is provided with a heat sink 8 for improving the heat release property. In this case, the lead frame 5 also serves as a circuit substrate. The semiconductor device 1 has a structure in which the above members 2 to 8 constituting the semiconductor device 1 are sealed by a plastic package 10. Some of the leads 4 are exposed to the outside of the plastic package 10.

Please replace the paragraph at page 14, lines 8-25, with the following rewritten paragraph:

These end leads 4a to 4d are respectively provided with a first lead portion 21 protruded from a plastic package 10, a second lead portion 22 located between the first lead portion 21 and gap-controlling portion 9, and a third lead portion 23 located at a position closer to the front end (outside) than the gap-controlling portion 9 so as to be inserted into the external substrate 25. In this case, widths (dimensions in the direction vertical to lead extending direction) of the second and third lead portions 22 and 23 are respectively smaller than the width of the first lead portion 21. Sectional areas (cross section vertical to the lead

extending direction) of the second and third lead portions 22 and 23 are smaller than the sectional area of the first lead portion 21. It is preferable that the length (dimension in the lead extending direction) of the gap-controlling portion 9 is smaller as long as the portion 9 has a strength capable of keeping the gap d constant.

Please replace the paragraph at page 16, lines 4-20, with the following rewritten paragraph:

As shown in FIGs. 4 and 5, the width of a portion 41 (hereafter referred to as "wide portion") located at a position closer to the center of the lead frame 5 than the tie bar 11 (hereafter referred to as "inside") is larger than the width of a portion 43 (hereafter referred to as "narrow portion") located at a position closer to the end of the lead frame than the tie bar 11 (hereafter referred to as "outside"). In the state of a final product, a part of the wide portion 41 protrudes outward from the plastic package 10 to form the first lead portion 21 serving as a part of the lead 4. Thus, by increasing the width of a portion of the lead 4 close to the plastic package 10 (hereafter referred to as "proximal portion") and improving the stiffness of the portion, the stiffness of the semiconductor device 1, particularly the stiffness of the semiconductor device 1 after mounted on the external substrate 25_2 is secured.

Please replace the paragraph at page 21, line 23 to page 22, line 11, with the following rewritten paragraph:

The embodiment 2 of the present invention will be described below by referring to FIGs. 8A and 8B to FIG. 10. The semiconductor device of the embodiment 2 has many points common to ~~thsoe~~ those of the embodiment 1 shown in FIGs. 1A-1D to FIG. 7. Therefore, to avoid duplication of description, points of the embodiment 2 different ~~form~~ from those of the embodiment 1 are mainly described below. In FIGs. 8A and 8B to FIG. 10, a member common to that of the embodiment 1 shown in FIGs. 1A-1D to FIG. 7 is provided

with the same reference number. Though a case is described below in which the shape of the gap-controlling portion 9 is rectangular, the shape is not restricted to a rectangle. A square, trapezoidal, or triangular shape is allowed as long as the shape can control a gap.

Please replace the paragraph at page 25, lines 2-12, with the following rewritten paragraph:

Also in the case of the semiconductor device 1 of the embodiment 2, it is possible to improve the solderability similarly to or more than the case of the semiconductor device 1 of the embodiment 1 when inserting the leads 4 into the external substrate 25, soldering the leads 4, and mounting the semiconductor device 1 on the external substrate 25 while securing the stiffness of the semiconductor device 1 after mounted on the external substrate 25, fabrication easiness of the semiconductor device 1, and alignment property when mounting the semiconductor device 1 on the external substrate 25.

Please replace the paragraph at page 34, line 25 to page 35, line11, with the following rewritten paragraph:

As shown in FIGs. 19A-19C and FIGs. 20A and 20B, a semiconductor device 61 of this embodiment 6 is different from the semiconductor device 1 of the embodiment 1 in configuration. That is, the semiconductor device 61 of the embodiment 6 is different from the semiconductor device 1 of the embodiment 1 in that heat sink 8 is joined to a lead frame 5, divided to be plural heat sinks 8, and constituted as a full molding structure in which the heat sinks 8 are completely included in a plastic package 10. However, other configurations of the semiconductor device 61 of the embodiment 6 are the same as those of the semiconductor device 1 of the embodiment 1.

Please replace the paragraph at page 36, line 18 to page 37, line11, with the following rewritten paragraph:

In the case of the embodiment 6, because the lead frame 5 is joined with the ~~head~~ heat sinks 8, an area for receiving the viscous force of a fluidic resin increases in a transfer molding step. Therefore, because the viscous force for deforming the lead frame 5 is increased, it is necessary to increase the stiffness of the leads 4 in order to prevent the deformation of the lead frame 5 due to increase of the viscous force. In particular, it is necessary that the stiffness of the first lead portion 21 close to the plastic package 10 is increased. However, because the leads 4 (including end leads 4a to 4d) of the semiconductor device 61 have a wide first lead portion 21, the portion 21 has a large stiffness and thereby, the easiness of fabrication of the semiconductor device 61 is not deteriorated. Moreover, as the leads 4 have a narrow second lead portion 22, a third lead portion 23 to be soldered, and a gap-controlling portion 9, it is possible to improve the solderability when mounting the semiconductor device 61 on the external substrate 25.